



**DC COMPONENTS CO., LTD.**  
RECTIFIER SPECIALISTS

**DL60P**

**TECHNICAL SPECIFICATIONS OF SMALL SIGNAL SCHOTTKY DIODES**

**FEATURES**

- \* Metal silicon junction, majority carrier conduction.
- \* High current capability, low forward voltage drop.
- \* Extremely low reverse current  $I_R$
- \* Ultra speed switching characteristics
- \* Small temperature coefficient of forward characteristics
- \* Satisfactory Wave detection efficiency
- \* For use in RECORDER, TV, RADIO, TELEPHONE as detectors, super high speed switching circuits, small current rectifier

**MECHANICAL DATA**

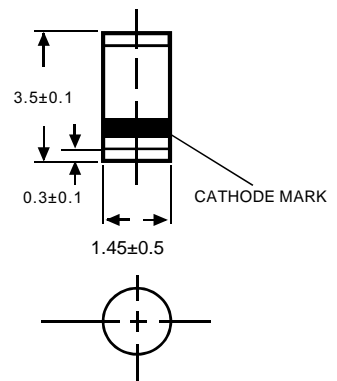
- \* Case: DL-35 glass case
- \* Polarity: color band denotes cathode end
- \* Weight: 0.05 grams approx.

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Ratings at 25°C ambient temperature unless otherwise specified.  
Single phase, half wave, 60 Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.



**DL-35**



Dimensions in millimeters

**ABSOLUTE RATINGS(LIMITING VALUES)**

PARAMETERS	SYMBOL	VALUE	UNITS
Zener Repetitive Peak Reverse Voltage	$V_{RRM}$	45	Volts
Forward Continuous Current	$I_F$	50	mA
Peak Forward Surge Current (t=1S)	$I_{FSM}$	500	mA
Storage and junction Temperature Range	$T_{STG}/T_J$	-65 to +125	°C
Maximum Lead Temperature for Soldering during 10S at 4mm from Case	$T_L$	230	°C

**ELECTRICAL CHARACTERISTICS**

PARAMETERS	TEST CONDITIONS	SYMBOL	VALUE		UNITS
			TYP.	MAX.	
Forward Voltage	$I_F = 1\text{mA}$	$V_F$	0.24	0.5	Volts
	$I_F = 200\text{mA}$		0.65	1.0	
Reverse Current	$V_R = 15\text{V}$	$I_R$	0.5	1.0	μA
Junction Capacitance	$V_R = 10\text{V}$ $f = 1\text{MHz}$	$C_J$	6.0		pF
Detection Efficiency	$V_I = 3\text{V}$ $f = 30\text{MHz}$ $C_L = 10\text{pF}$ $R_L = 3.8\text{K}\Omega$	$\eta$	60		%
Reverse Recovery time	$I_F = I_R = 1\text{mA}$ $I_{rr} = 1\text{mA}$ $R_C = 100\Omega$	$t_{rr}$		1	ns
Junction Ambient Thermal Resistance		$R_{\theta JA}$	400		°C/W